

NZQA5V6XV5T1 Series

Quad Array for ESD Protection

This quad monolithic silicon voltage suppressor is designed for applications requiring transient overvoltage protection capability. It is intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment, and other applications. Its quad junction common anode design protects four separate lines using only one package. These devices are ideal for situations where board space is at a premium.

Specification Features

- SOT-553 Package Allows Four Separate Unidirectional Configurations
- Low Leakage < 1 μ A @ 3 Volt for NZQA5V6XV5T1
- Breakdown Voltage: 5.6 Volt - 6.8 Volt @ 1 mA
- ESD Protection Meeting IEC61000-4-2 - Level 4

Mechanical Characteristics

- Void Free, Transfer-Molded, Thermosetting Plastic Case
- Corrosion Resistant Finish, Easily Solderable
- Package Designed for Optimal Automated Board Assembly
- Small Package Size for High Density Applications
- 100% Lead Free, MSL1 @ 260°C Reflow Temperature



ON Semiconductor®

<http://onsemi.com>

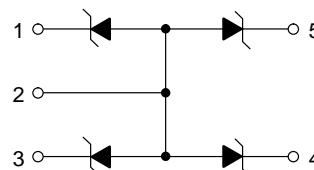


SOT-553
CASE 463B
PLASTIC

MARKING DIAGRAM



xx = Device Marking
D = One Digit Date Code



ORDERING INFORMATION

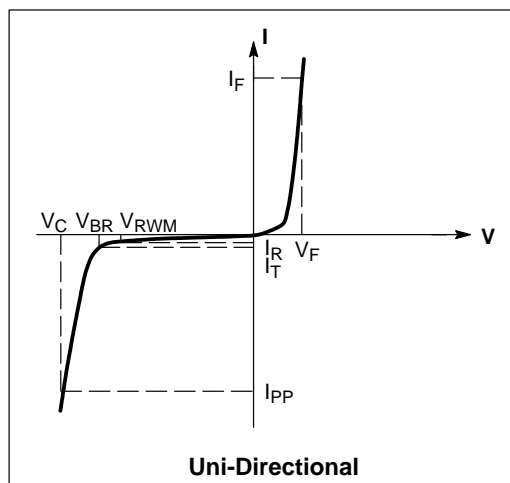
Device	Package	Shipping
NZQA5V6XV5T1	SOT-553	4000/Tape & Reel
NZQA6V2XV5T1	SOT-553	4000/Tape & Reel
NZQA6V8XV5T1	SOT-553	4000/Tape & Reel

NZQA5V6XV5T1 Series

ELECTRICAL CHARACTERISTICS

($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
Θ_{VBR}	Maximum Temperature Coefficient of V_{BR}
I_F	Forward Current
V_F	Forward Voltage @ I_F
Z_{ZT}	Maximum Zener Impedance @ I_{ZT}
I_{ZK}	Reverse Current
Z_{ZK}	Maximum Zener Impedance @ I_{ZK}



MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Value	Unit
Peak Power Dissipation (8 X 20 μs @ $T_A = 25^\circ\text{C}$) (Note 1)	P_{PK}	100	W
Steady State Power - 1 Diode (Note 2)	P_D	300	mW
Thermal Resistance Junction to Ambient Above 25°C , Derate	$R_{\theta JA}$	370 2.7	$^\circ\text{C/W}$ mW/ $^\circ\text{C}$
Maximum Junction Temperature	T_{Jmax}	150	$^\circ\text{C}$
Operating Junction and Storage Temperature Range	$T_J T_{stg}$	-55 to +150	$^\circ\text{C}$
ESD Discharge MIL STD 883C - Method 3015-6 IEC1000-4-2, Air Discharge IEC1000-4-2, Contact Discharge	V_{PP}	16 16 9	kV
Lead Solder Temperature (10 seconds duration)	T_L	260	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

Device	Device Marking	Breakdown Voltage V_{BR} @ 1 mA (Volts)			Leakage Current I_{RM} @ V_{RM}		V_C Max @ I_{PP}		Typ Capacitance @ 0 V Bias (Note 3) (pF)	Max V_F @ $I_F = 200$ mA (V)
		Min	Nom	Max	V_{RWM}	I_{RWM} (μA)	V_C (V)	I_{PP} (A)		
NZQA5V6XV5T1	56	5.32	5.6	5.88	3.0	1.0	10.5	10	90	1.3
NZQA6V2XV5T1	62	5.89	6.2	6.51	4.0	0.5	11.5	9.0	80	1.3
NZQA6V8XV5T1	68	6.46	6.8	7.14	4.3	0.1	12.5	8.0	70	1.3

1. Non-repetitive current per Figure 1.
2. Only 1 diode under power. For all 4 diodes under power, P_D will be 25%. Mounted on FR-4 board with min pad.
3. Capacitance of one diode at $f = 1$ MHz, $V_R = 0$ V, $T_A = 25^\circ\text{C}$

NZQA5V6XV5T1 Series

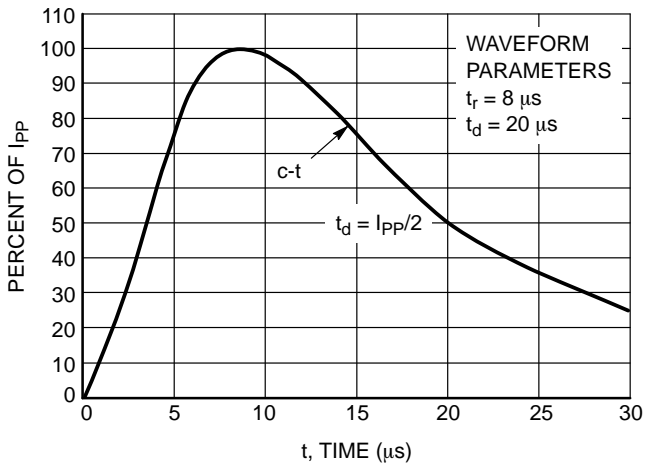


Figure 1. Pulse Waveform

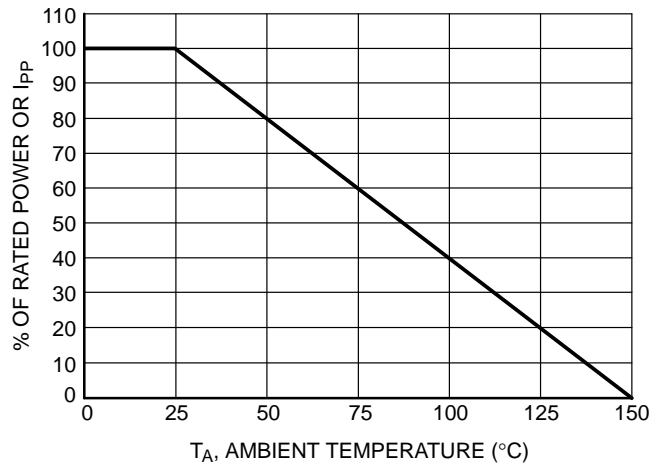


Figure 2. Power Derating Curve

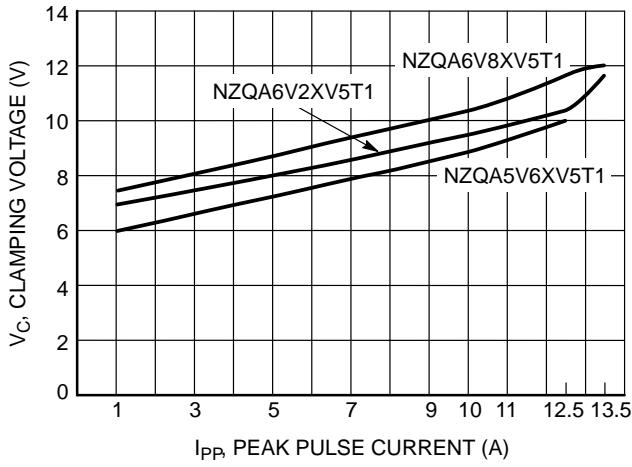


Figure 3. Clamping Voltage versus Peak Pulse Current

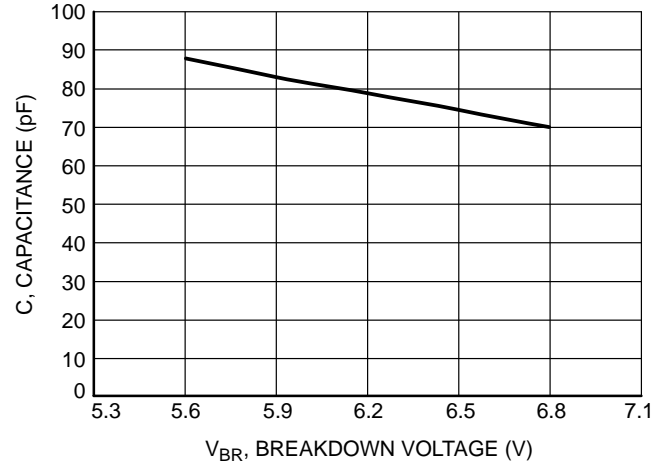
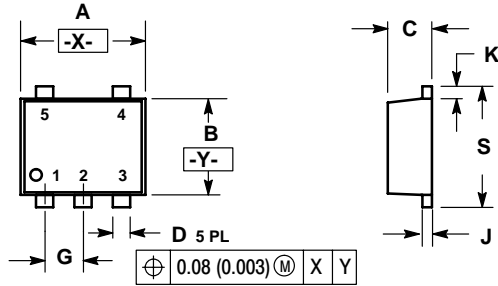


Figure 4. Typical Capacitance

NZQA5V6XV5T1 Series

PACKAGE DIMENSIONS

SOT-553, 5-LEAD
CASE 463B-01
ISSUE O



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.


DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.50	1.70	0.059	0.067
B	1.10	1.30	0.043	0.051
C	0.50	0.60	0.020	0.024
D	0.17	0.27	0.007	0.011
G	0.50 BSC		0.020 BSC	
J	0.08	0.18	0.003	0.007
K	0.10	0.30	0.004	0.012
S	1.50	1.70	0.059	0.067

STYLE 1:

- PIN 1. BASE 1
- EMITTER 1/2
- BASE 2
- COLLECTOR 2
- COLLECTOR 1

STYLE 2:

- PIN 1. CATHODE
- ANODE
- CATHODE
- CATHODE
- CATHODE

ON Semiconductor and  are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

Literature Fulfillment:

Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: ONlit@hibbertco.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

JAPAN: ON Semiconductor, Japan Customer Focus Center
2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051
Phone: 81-3-5773-3850

ON Semiconductor Website: <http://onsemi.com>

For additional information, please contact your local Sales Representative.